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M53210124CE2/CJ2 with Fast Page Mode

1M x 32 DRAM SIMM using 1Mx16, 1K Refresh, 5V

GENERAL DESCRIPTION

The Samsung M53210124C is a 1Mx32bits Dynamic RAM high density memory module. The Samsung M53210124C consists of two CMOS 1Mx16bits DRAMs in 42-pin SOJ packages mounted on a 72-pin glass-epoxy substrate. A 0.1 or 0.22uF decoupling capacitor is mounted on the printed circuit board for each DRAM. The M53210124C is a Single In-line Memory Module with edge connections and is intended for mounting into 72 pin edge connector sockets.

FEATURES

- Part Identification
  - M53210124CE2-C(1024 cycles/16ms Ref, SOJ, Solder)
  - M53210124CJ2-C(1024 cycles/16ms Ref, SOJ, Gold)
- Fast Page Mode Operation
- $\overline{\text{CAS}}$-before-$\overline{\text{RAS}}$ refresh capability
- $\overline{\text{RAS}}$-only refresh capability
- TTL compatible inputs and outputs
- Single +5V±10% power supply
- JEDEC standard PDPin & pinout
- PCB : Height(750mil), single sided component

PERFORMANCE RANGE

Speed	t_{RAC}	t_{CAC}	t_{RC}
-50	50ns	15ns	90ns
-60	60ns	15ns	110ns

PIN CONFIGURATIONS

Pin	Symbol	Pin	Symbol
1	Vss	37	NC
2	DQ0	38	NC
3	DQ16	39	$\overline{\text{Vss}}$
4	DQ1	40	$\overline{\text{CAS0}}$
5	DQ17	41	$\overline{\text{CAS2}}$
6	DQ2	42	$\overline{\text{CAS3}}$
7	DQ18	43	$\overline{\text{CAS1}}$
8	DQ3	44	$\overline{\text{RAS0}}$
9	DQ19	45	Res($\overline{\text{RAS1}}$)
10	Vcc	46	$\overline{\text{NC}}$
11	NC	47	$\overline{\text{W}}$
12	A0	48	NC
13	A1	49	DQ8
14	A2	50	DQ24
15	A3	51	DQ9
16	A4	52	DQ25
17	A5	53	DQ10
18	A6	54	DQ26
19	Res(A10)	55	DQ11
20	DQ4	56	DQ27
21	DQ20	57	DQ12
22	DQ5	58	DQ28
23	DQ21	59	Vcc
24	DQ6	60	DQ29
25	DQ22	61	DQ13
26	DQ7	62	DQ30
27	DQ23	63	DQ14
28	A7	64	DQ31
29	Res(A11)	65	DQ15
30	Vcc	66	NC
31	A8	67	PD1
32	$\overline{\text{A9}}$	68	PD2
33	Res($\overline{\text{RAS1}}$)	69	PD3
34	RAS0	70	PD4
35	NC	71	NC
36	NC	72	Vss

PIN NAMES

Pin Name	Function
A0 - A9	Address Inputs
DQ0 - DQ31	Data In/Out
$\overline{\text{W}}$	Read/Write Enable
$\overline{\text{RAS0}}$	Row Address Strobe
$\overline{\text{CAS0}}$ - $\overline{\text{CAS3}}$	Column Address Strobe
PD1 -PD4	Presence Detect
Vcc	Power(+5V)
Vss	Ground
NC	No Connection
Res	Reserved Pin

PRESENCE DETECT PINS (Optional)

Pin	50NS	60NS
PD1	Vss	Vss
PD2	Vss	Vss
PD3	Vss	NC
PD4	Vss	NC

* Pin connection changing available

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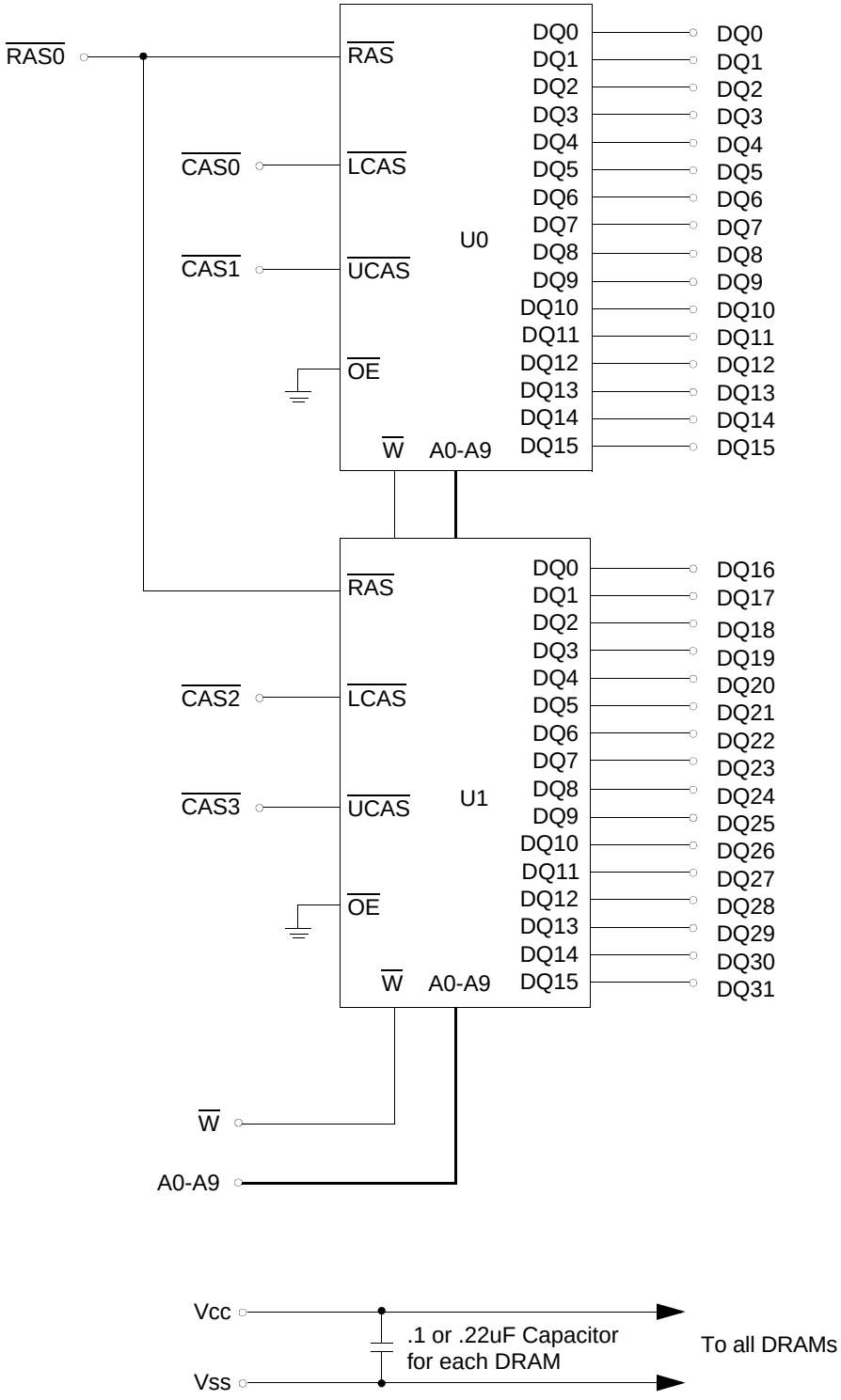
FUNCTIONAL BLOCK DIAGRAM



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ABSOLUTE MAXIMUM RATINGS *

Item	Symbol	Rating	Unit
Voltage on any pin relative to V_{SS}	V_{IN}, V_{OUT}	-1 to +7.0	V
Voltage on V_{CC} supply relative to V_{SS}	V_{CC}	-1 to +7.0	V
Storage Temperature	T_{stg}	-55 to +150	°C
Power Dissipation	P_d	2	W
Short Circuit Output Current	I_{OS}	50	mA

* Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to the conditions as detailed in the operational sections of this data sheet. Exposure to absolute maximum rating conditions for intended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS (Voltage referenced to V_{SS}, T_A = 0 to 70°C)

Item	Symbol	Min	Typ	Max	Unit
Supply Voltage	V_{CC}	4.5	5.0	5.5	V
Ground	V_{SS}	0	0	0	V
Input High Voltage	V_{IH}	2.4	-	V_{CC}+1[*1]	V
Input Low Voltage	V_{IL}	-1.0[*2]	-	0.8	V

*1 : V_{CC}+2.0V/20ns, Pulse width is measured at V_{CC}.

*2 : -2.0V/20ns, Pulse width is measured at V_{SS}.

DC AND OPERATING CHARACTERISTICS (Recommended operating conditions unless otherwise noted)

Symbol	Speed	M53210124CE2/CJ2		Unit
		Min	Max	
I_{CC1}	-50 -60	- -	300 280	mA mA
I_{CC2}	Don't care	-	4	mA
I_{CC3}	-50 -60	- -	300 280	mA mA
I_{CC4}	-50 -60	- -	180 160	mA mA
I_{CC5}	Don't care	-	2	mA
I_{CC6}	-50 -60	- -	300 280	mA mA
$I_{I(L)}$ $I_{O(L)}$	Don't care	-10 -5	10 5	uA uA
V_{OH} V_{OL}	Don't care	2.4 -	- 0.4	V V

I_{CC1} : Operating Current * ($\overline{RAS}$, $\overline{LCAS}$ or $\overline{UCAS}$, Address cycling @t_{RC}=min)

I_{CC2} : Standby Current ($\overline{RAS}$=$\overline{LCAS}$=$\overline{UCAS}$=$\overline{W}$=V_{IH})

I_{CC3} : $\overline{RAS}$ Only Refresh Current * ($\overline{LCAS}$=$\overline{UCAS}$=V_{IH}, $\overline{RAS}$ cycling @t_{RC}=min)

I_{CC4} : Fast Page Mode Current * ($\overline{RAS}$=V_{IL}, $\overline{LCAS}$ or $\overline{UCAS}$ cycling : t_{PC}=min)

I_{CC5} : Standby Current ($\overline{RAS}$=$\overline{LCAS}$=$\overline{UCAS}$=$\overline{W}$=Vcc-0.2V)

I_{CC6} : $\overline{CAS}$-Before-$\overline{RAS}$ Refresh Current * ($\overline{RAS}$ and $\overline{CAS}$ cycling @t_{RC}=min)

$I_{I(L)}$: Input Leakage Current (Any input 0≤V_{IN}≤Vcc+0.5V, all other pins not under test=0 V)

$I_{O(L)}$: Output Leakage Current(Data Out is disabled, 0V≤V_{OUT}≤Vcc)

V_{OH} : Output High Voltage Level (I_{OH} = -5mA)

V_{OL} : Output Low Voltage Level (I_{OL} = 4.2mA)

*** NOTE** : I_{CC1}, I_{CC3}, I_{CC4} and I_{CC6} are dependent on output loading and cycle rates. Specified values are obtained with the output open. I_{CC} is specified as an average current. In I_{CC1} and I_{CC3}, address can be changed maximum once while $\overline{RAS}$=V_{IL}. In I_{CC4}, address can be changed maximum once within one page mode cycle, t_{PC}.

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CAPACITANCE (T_A = 25°C, V_{CC}=5V, f = 1MHz)

Item	Symbol	Min	Max	Unit
Input capacitance[A0-A9]	C_{IN1}	-	30	pF
Input capacitance[$\overline{W}$]	C_{IN2}	-	30	pF
Input capacitance[$\overline{RAS0}$]	C_{IN3}	-	25	pF
Input capacitance[$\overline{CAS0}$ - $\overline{CAS3}$]	C_{IN4}	-	20	pF
Input/Output capacitance[DQ0-31]	C_{DQ}	-	20	pF

AC CHARACTERISTICS (0°C≤T_A≤70°C, V_{CC}=5.0V±10%. See notes 1,2.)

Test condition : V_{ih}/V_{il}=2.4/0.8V, V_{oh}/V_{ol}=2.4/0.4V, output loading CL=100pF

Parameter	Symbol	-50		-60		Unit	Note
		Min	Max	Min	Max		
Random read or write cycle time	t_{RC}	90		110		ns	
Access time from $\overline{RAS}$	t_{RAC}		50		60	ns	3,4
Access time from $\overline{CAS}$	t_{CAC}		15		15	ns	3,4,5
Access time from column address	t_{AA}		25		30	ns	3,10
$\overline{CAS}$ to output in Low-Z	t_{CLZ}	0		0		ns	3
Output buffer turn-off delay	t_{OFF}	0	13	0	15	ns	6
Transition time(rise and fall)	t_T	3	50	3	50	ns	2
$\overline{RAS}$ precharge time	t_{RP}	30		40		ns	
$\overline{RAS}$ pulse width	t_{RAS}	50	10K	60	10K	ns	
$\overline{RAS}$ hold time	t_{RSH}	13		15		ns	
$\overline{CAS}$ hold time	t_{CSH}	50		60		ns	
$\overline{CAS}$ pulse width	t_{CAS}	13	10K	15	10K	ns	
$\overline{RAS}$ to $\overline{CAS}$ delay time	t_{RCD}	20	37	20	45	ns	4
$\overline{RAS}$ to column address delay time	t_{RAD}	15	25	15	30	ns	10
$\overline{CAS}$ to $\overline{RAS}$ precharge time	t_{CRP}	5		5		ns	
Row address set-up time	t_{ASR}	0		0		ns	
Row address hold time	t_{RAH}	10		10		ns	
Column address set-up time	t_{ASC}	0		0		ns	
Column address hold time	t_{CAH}	10		10		ns	
Column address to $\overline{RAS}$ lead time	t_{RAL}	25		30		ns	
Read command set-up time	t_{RCS}	0		0		ns	
Read command hold referenced to $\overline{CAS}$	t_{RCH}	0		0		ns	8
Read command hold referenced to $\overline{RAS}$	t_{RRH}	0		0		ns	8
Write command hold time	t_{WCH}	10		10		ns	
Write command pulse width	t_{WP}	10		10		ns	
Write command to $\overline{RAS}$ lead time	t_{RWL}	13		15		ns	
Write command to $\overline{CAS}$ lead time	t_{CWL}	13		15		ns	
Data-in set-up time	t_{DS}	0		0		ns	9
Data-in hold time	t_{DH}	10		10		ns	9
Refresh period	t_{REF}		16		16	ms	
Write command set-up time	t_{WCS}	0		0		ns	7
$\overline{CAS}$ setup time($\overline{CAS}$-before-$\overline{RAS}$ refresh)	t_{CSR}	5		5		ns	
$\overline{CAS}$ hold time($\overline{CAS}$-before-$\overline{RAS}$ refresh)	t_{CHR}	10		10		ns	
$\overline{RAS}$ precharge to $\overline{CAS}$ hold time	t_{RPC}	5		5		ns	
Access time from $\overline{CAS}$ precharge	t_{CPA}		30		35	ns	3

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AC CHARACTERISTICS (0°C≤TA≤70°C, VCC=5.0V±10%. See notes 1,2.)

Test condition : Vih/Vil=2.4/0.8V, Voh/Vol=2.4/0.4V, output loading CL=100pF

Parameter	Symbol	-50		-60		Unit	Note
		Min	Max	Min	Max		
Fast page mode cycle time	t_{PC}	35		40		ns	
$\overline{CAS}$ precharge time(Fast page cycle)	t_{CP}	10		10		ns	
$\overline{RAS}$ pulse width(Fast page cycle)	t_{RASP}	50	200K	60	200K	ns	
$\overline{W}$ to $\overline{RAS}$ precharge time(C-B-R refresh)	t_{WRP}	10		10		ns	
$\overline{W}$ to $\overline{RAS}$ hold time(C-B-R refresh)	t_{WRH}	10		10		ns	

NOTES

1. An initial pause of 200us is required after power-up followed by any 8 $\overline{RAS}$-only or $\overline{CAS}$-before-$\overline{RAS}$ refresh cycles before proper device operation is achieved.
2. V_{IH}(min) and V_{IL}(max) are reference levels for measuring timing of input signals. Transition times are measured between V_{IH}(min) and V_{IL}(max) and are assumed to be 5ns for all inputs.
3. Measured with a load equivalent to 2 TTL loads and 100pF.
4. Operation within the t_{RCD}(max) limit insures that t_{RAC}(max) can be met. t_{RCD}(max) is specified as a reference point only. If t_{RCD} is greater than the specified t_{RCD}(max) limit, then access time is controlled exclusively by t_{CAC}.
5. Assumes that $t_{RCD} \geq t_{RCD}$(max).
6. This parameter defines the time at which the output achieves the open circuit condition and is not referenced to V_{OH} or V_{OL}.
7. t_{WCS} is non-restrictive operating parameter. It is included in the data sheet as electrical characteristics only. If $t_{WCS} \geq t_{WCS}$(min), the cycle is an early write cycle and the data out pin will remain high impedance for the duration of the cycle.
8. Either t_{RCH} or t_{RRH} must be satisfied for a read cycle.
9. These parameter are referenced to the $\overline{CAS}$ leading edge in early write cycles.
10. Operation within the t_{RAD}(max) limit insures that t_{RAC}(max) can be met. t_{RAD}(max) is specified as reference point only. If t_{RAD} is greater than the specified t_{RAD}(max) limit, then access time is controlled by t_{AA}.

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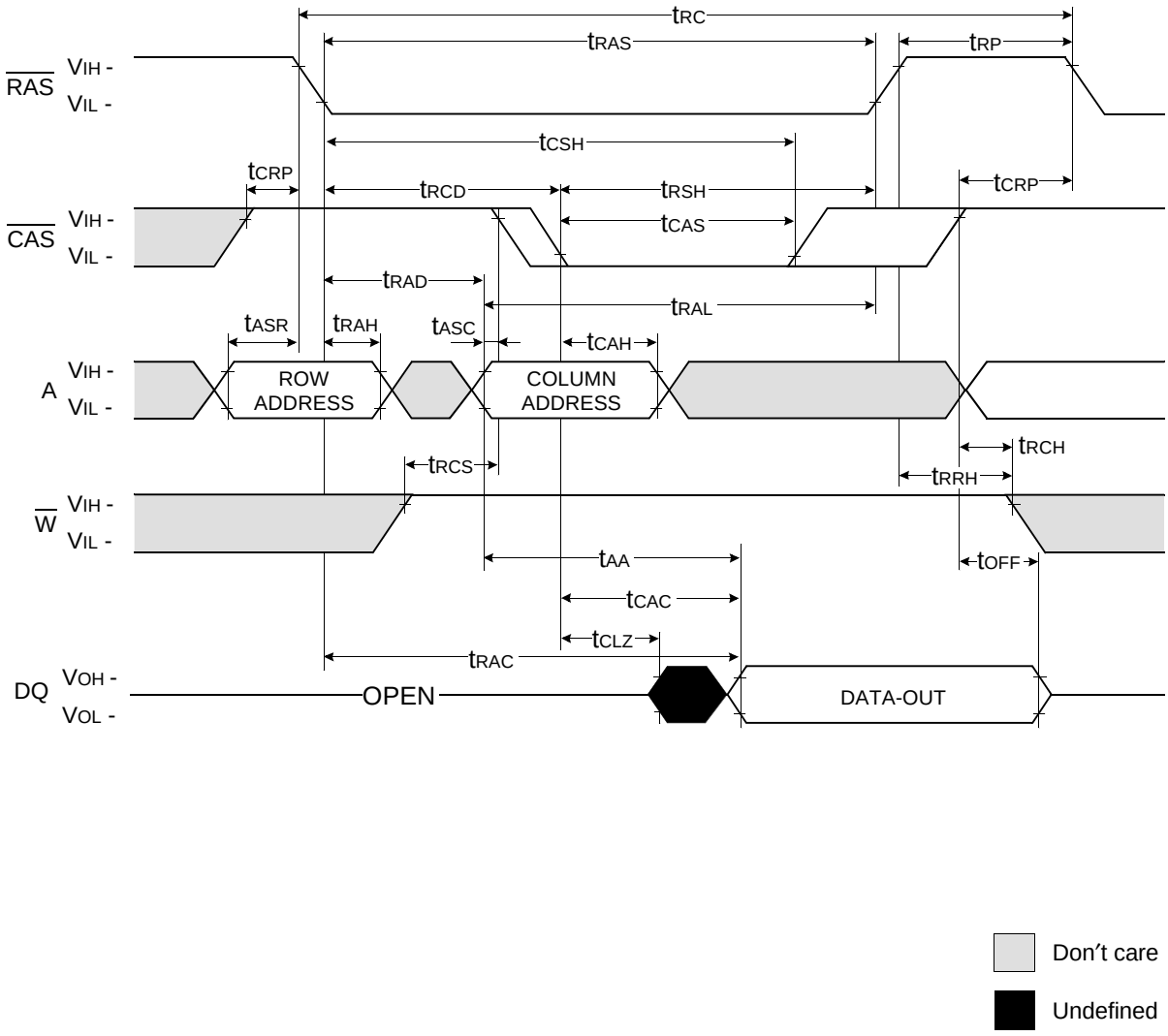
READ CYCLE



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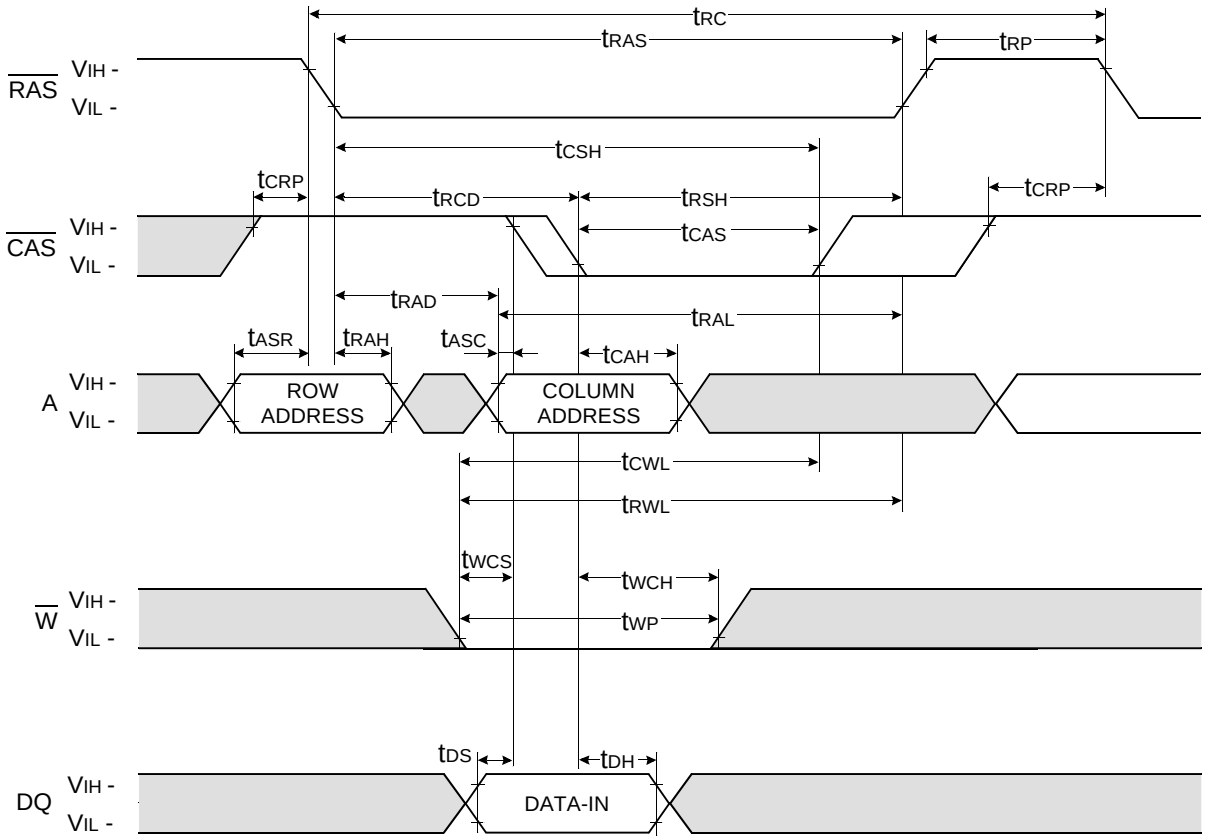
WRITE CYCLE (EARLY WRITE)

NOTE : DOUT = OPEN



Don't care

Undefined

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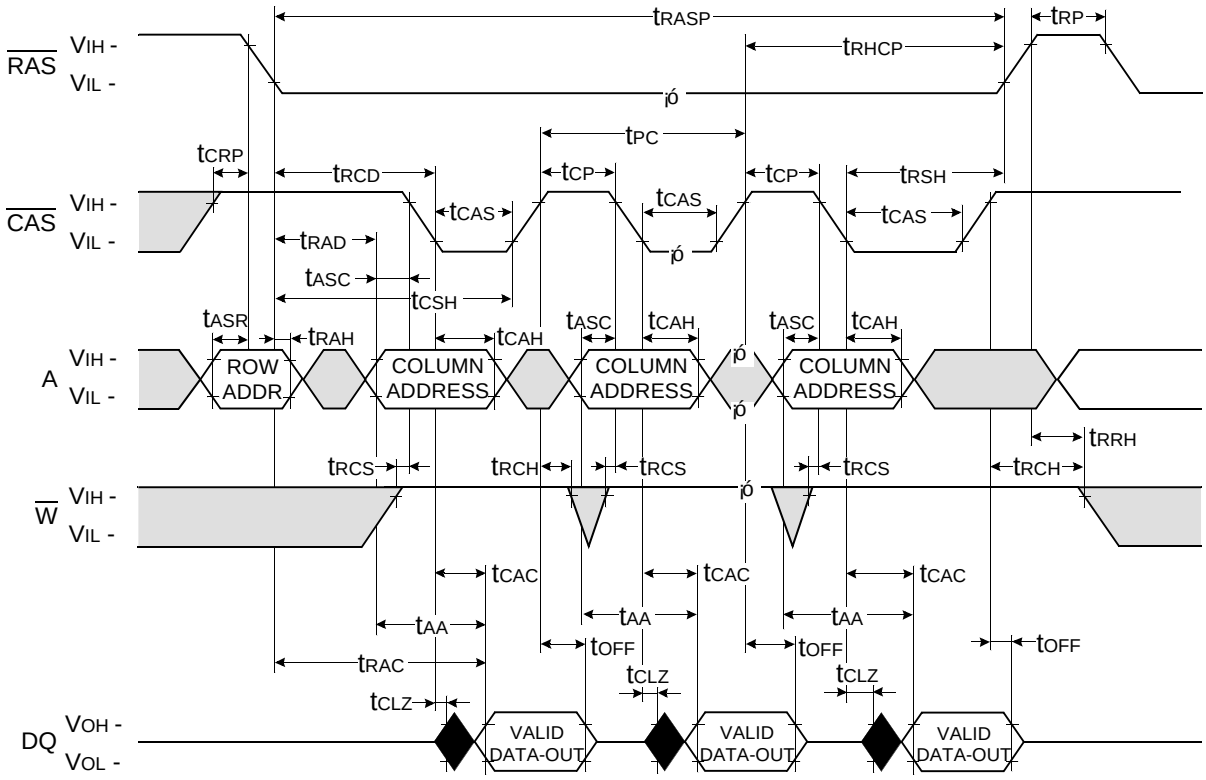
FAST PAGE READ CYCLE

NOTE : DOUT = OPEN



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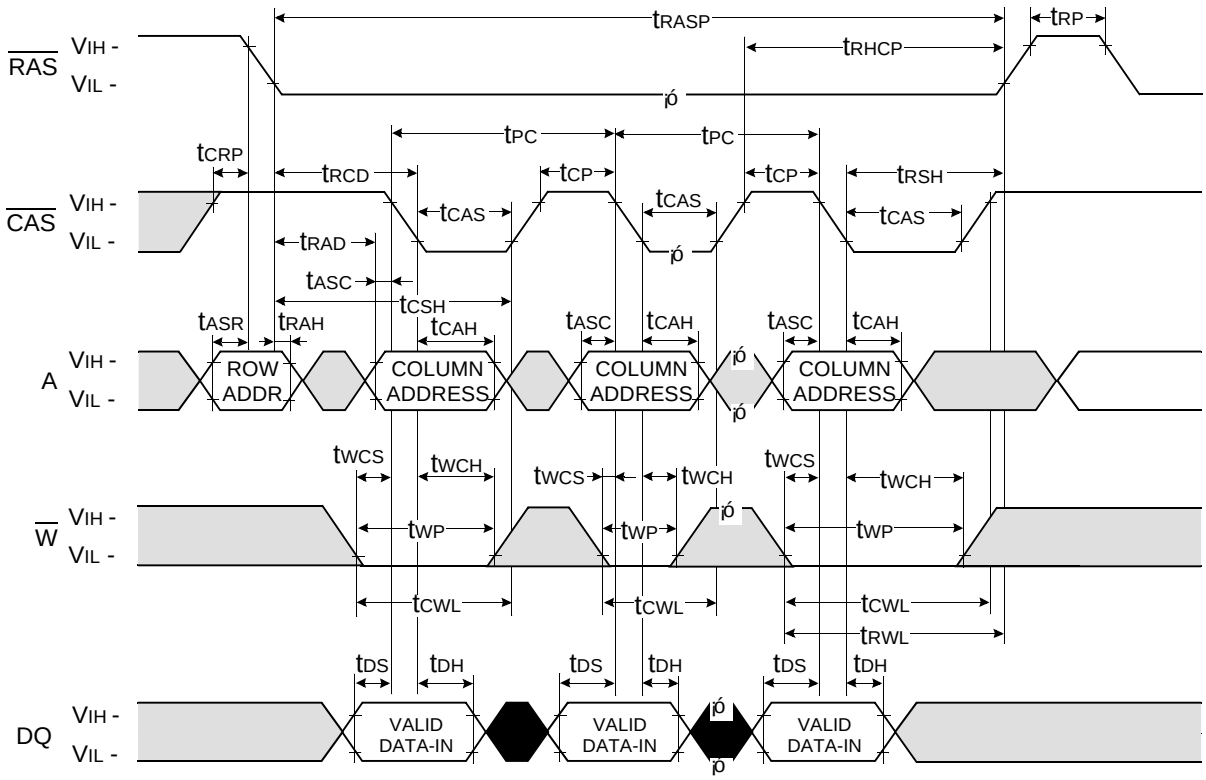
FAST PAGE WRITE CYCLE (EARLY WRITE)

NOTE : DOUT = OPEN



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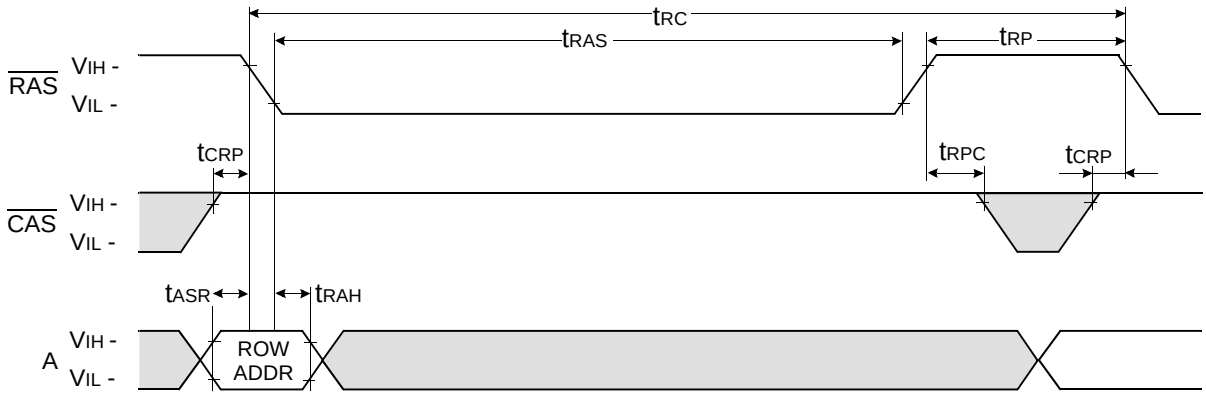
$\overline{RAS}$ - ONLY REFRESH CYCLE

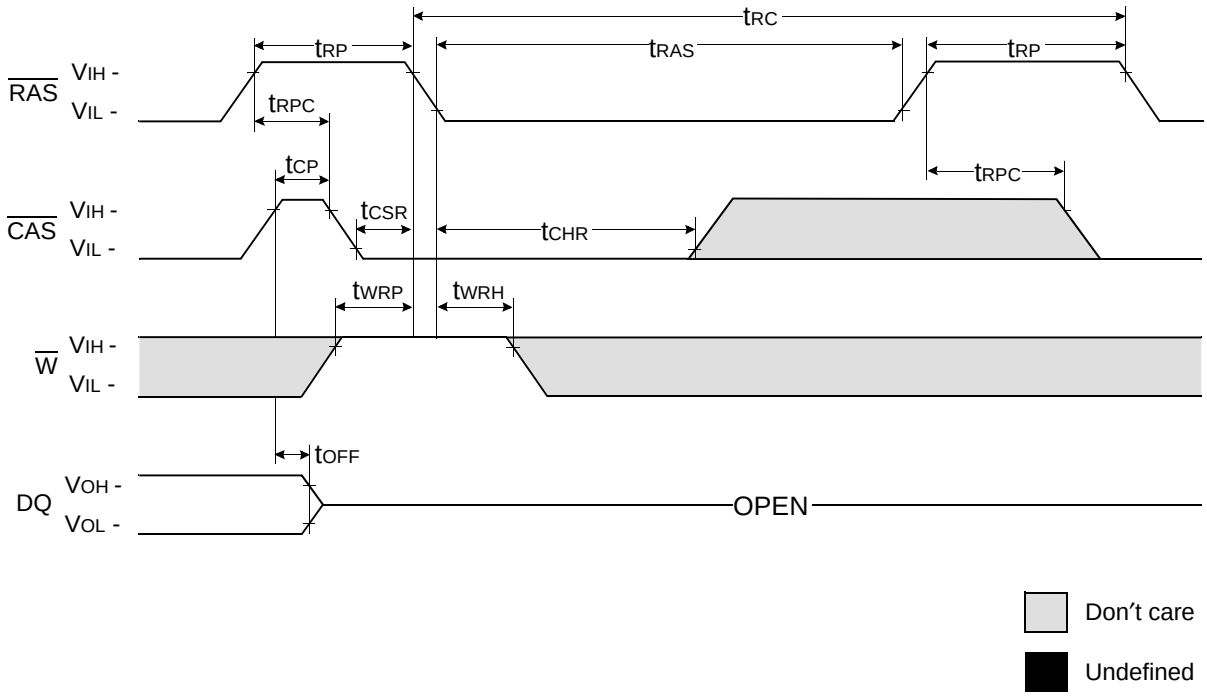
NOTE : $\overline{W}$, $\overline{OE}$, D_{IN} = Don't care

D_{OUT} = OPEN



$\overline{CAS}$ - BEFORE - $\overline{RAS}$ REFRESH CYCLE

NOTE : $\overline{OE}$, A = Don't care



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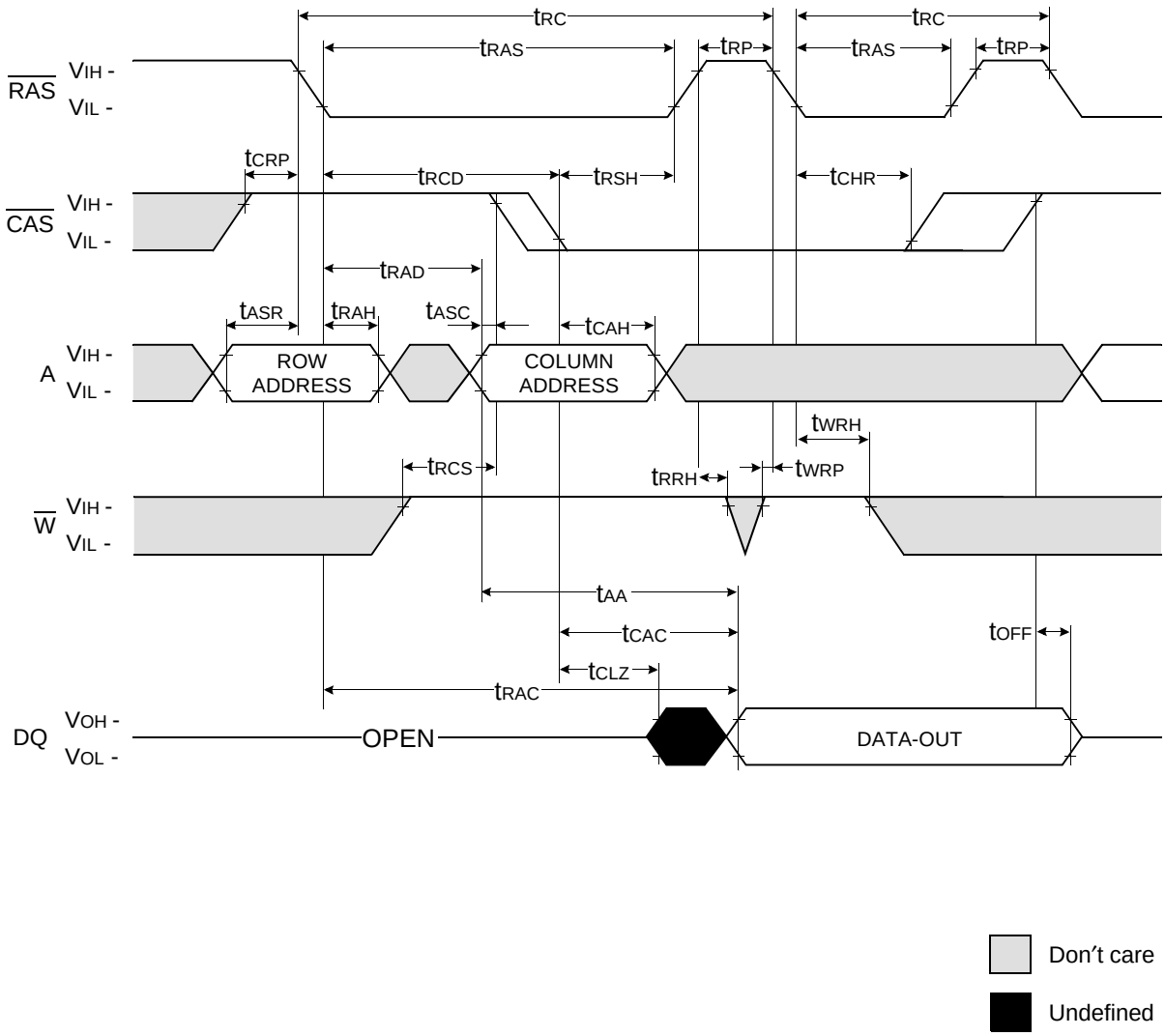
HIDDEN REFRESH CYCLE (READ)



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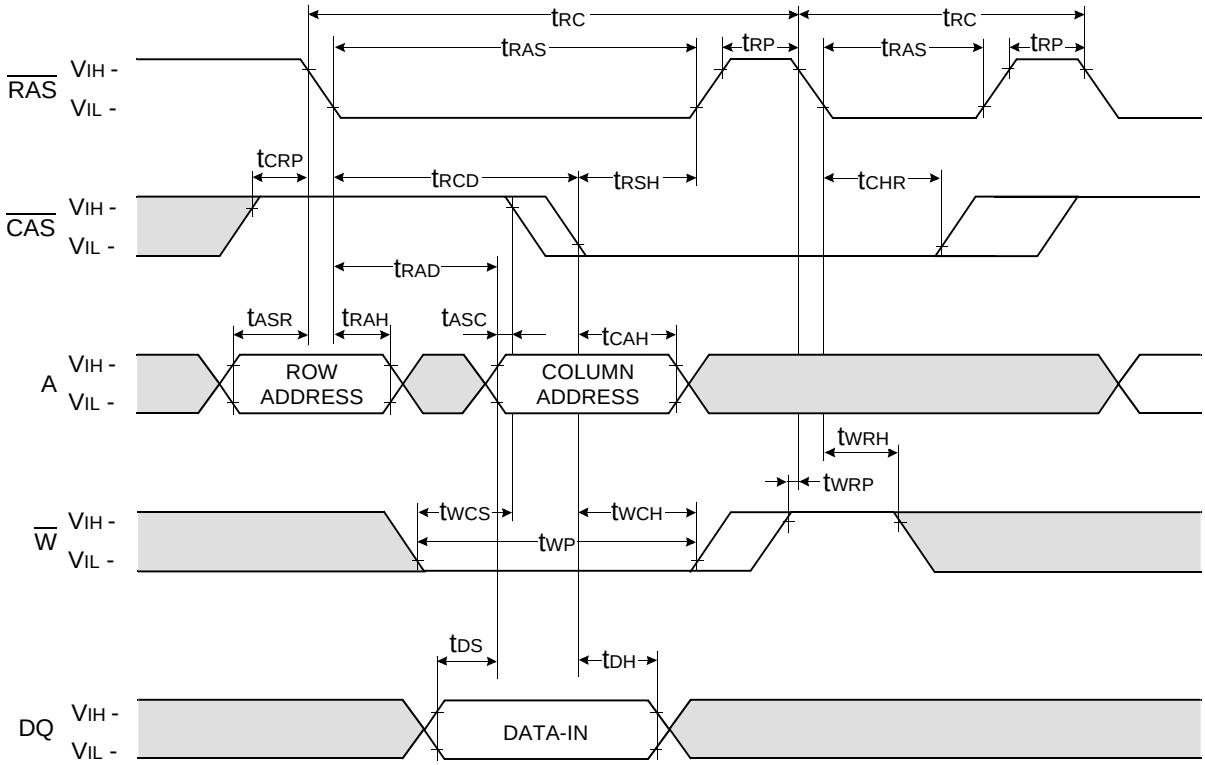
HIDDEN REFRESH CYCLE (WRITE)

NOTE : DOUT = OPEN



Don't care

Undefined

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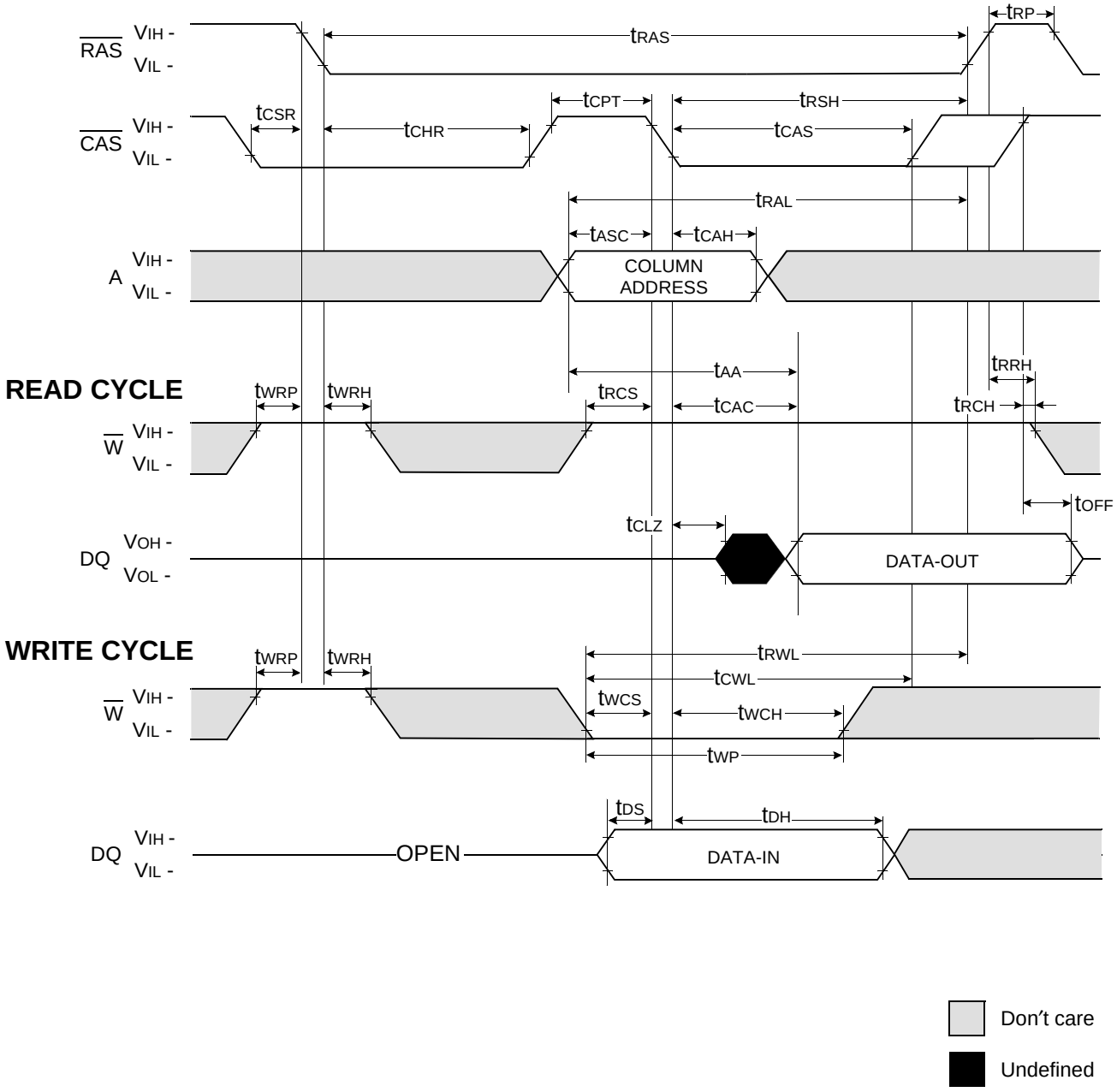
CAS-BEFORE-RAS REFRESH COUNTER TEST CYCLE



NOTE : This timing diagram is applied to all devices besides 16M DRAM 4th & 64M DRAM.

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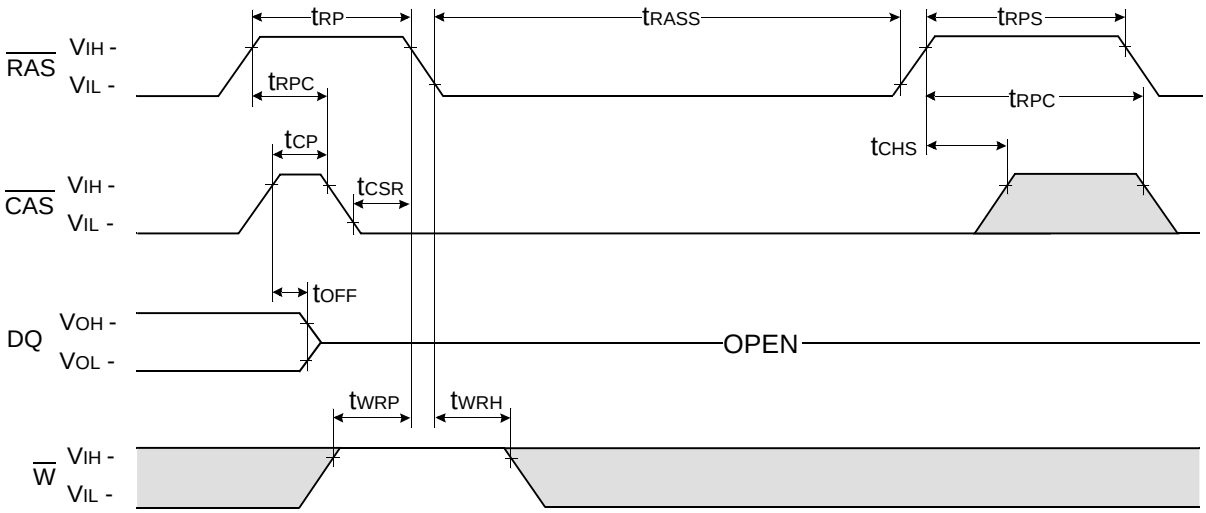
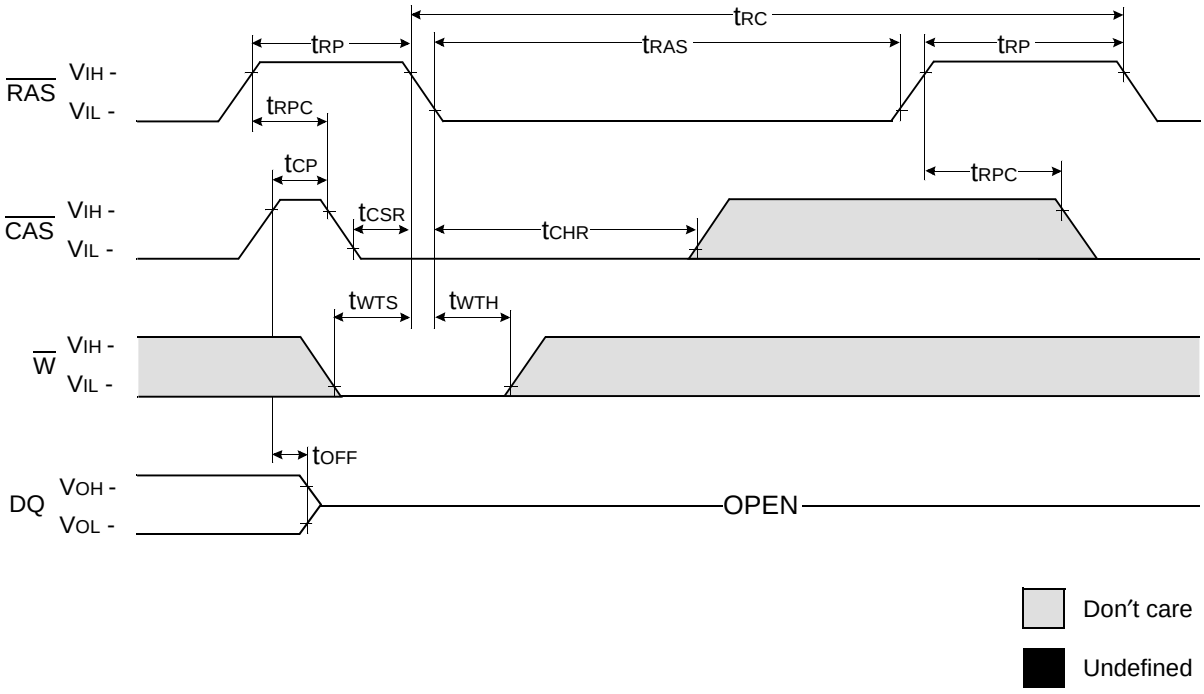
$\overline{CAS}$ - BEFORE - $\overline{RAS}$ SELF REFRESH CYCLE

NOTE : $\overline{OE}$, A = Don't care



TEST MODE IN CYCLE

NOTE : $\overline{OE}$, A = Don't care



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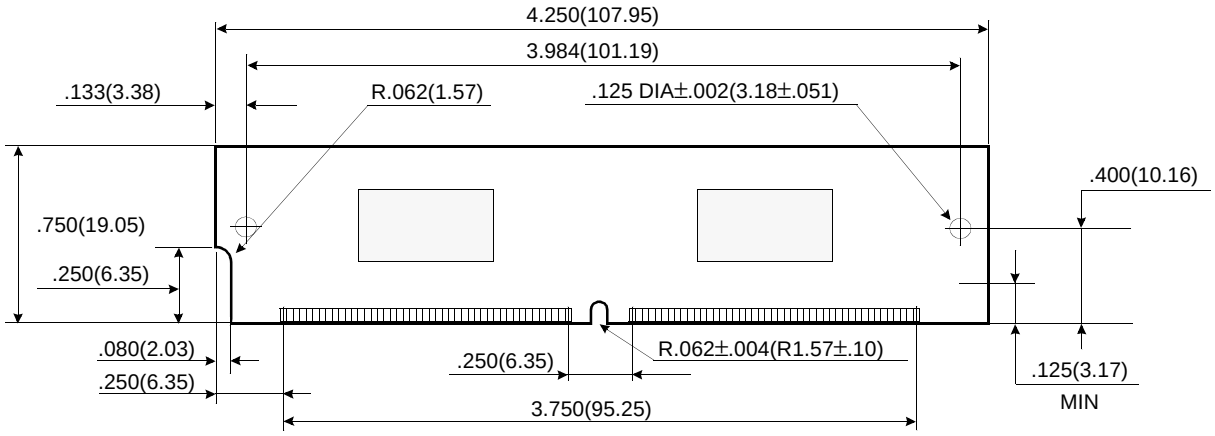
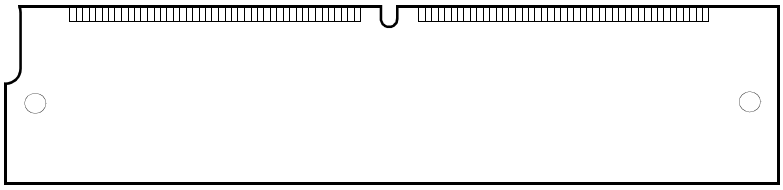
PACKAGE DIMENSIONS

Units : Inches (millimeters)

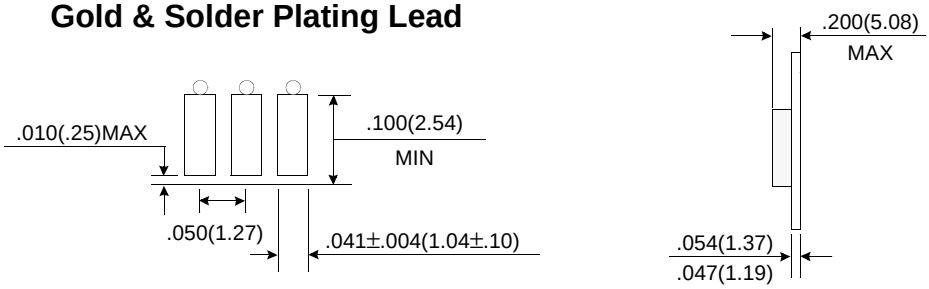


(Front view)



(Back view)

Gold & Solder Plating Lead



Tolerances : ±.005(.13) unless otherwise specified

NOTE : The used device is 1Mx16 DRAM
DRAM Part No. : M53210124CE2/CJ2 -- K4F151611C-J(400 mil)

Revision History
Rev 0.0 : Oct. 1999